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(54) **LIGHT DETECTING DEVICE AND ELECTRONIC DEVICE**

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(57) **ABSTRACT**

A light detecting device includes a semiconductor layer having a first surface and a second surface located on opposite sides to each other in a thickness direction, and a photoelectric conversion cell provided in the semiconductor layer and partitioned by a first isolation region. The photoelectric conversion cell includes a first photoelectric conversion region adjacent to a second photoelectric conversion region in plan view and each having a photoelectric conversion unit and a transfer transistor, a second isolation region arranged between the first photoelectric conversion region and the second photoelectric conversion region in plan view and extending in a thickness direction of the semiconductor layer, and an element formation region partitioned on the first surface side of the semiconductor layer by a third isolation region and provided with a pixel transistor. The element formation region extends over the first and second photoelectric conversion regions in plan view.